TAYCHIPST

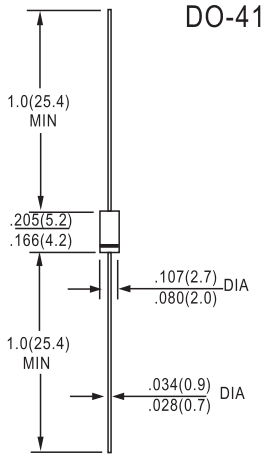
SILICON RECTIFIER DIODES

S5277B THRU S5277N

100V-1000V 1.0A

FEATURES

* High current capability
* High surge current capability
* High reliability
* Low reverse current
* Low forward voltage drop
* Pb / RoHS Free



Dimensions in inches and (millimeters)

Mechanical Data

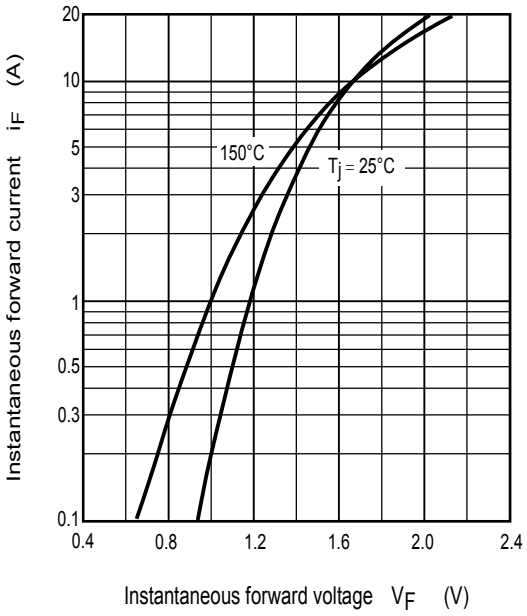
* Case : DO-41 Molded plastic
* Epoxy : UL94V-O rate flame retardant
* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
* Polarity : Color band denotes cathode end
* Mounting position : Any
* Weight : 0.339 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

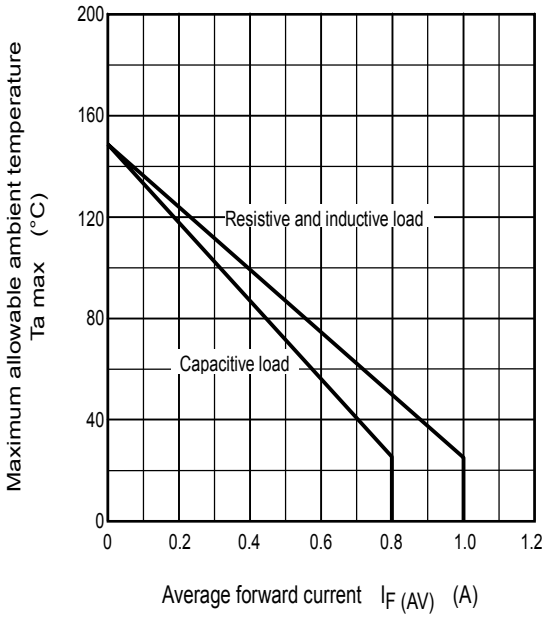
Rating at 25°C ambient temperature unless otherwise specified.

RATING	SYMBOL	S5277B	S5277G	S5277J	S5277N	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	400	600	1000	V
Maximum Average Forward Current	$I_{F(AV)}$	1.0				A
Maximum Peak One Cycle Surge Forward Current		(50Hz)	(60Hz)	(50Hz)	(60Hz)	
(Non-Repetitive)	I_{FSM}	50	55	30	33	A
Peak Forward Voltage at I_F = 1.0 A	V_F	1.2				V
Repetitive Peak Reverse Current	I_{RRM}	10				µA
Thermal Resistance (Junction to Ambient)	$R_{th\ (j-a)}$	120				°C/W
Junction Temperature Range	T_J	- 40 to + 150				°C
Storage Temperature Range	T_{STG}	- 40 to + 150				°C

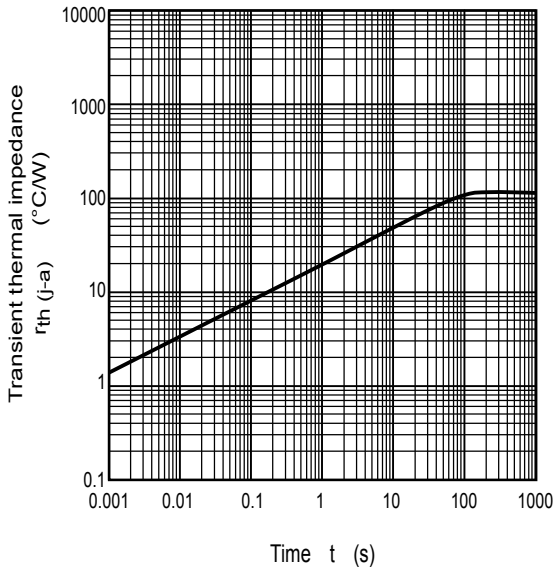
$i_F - v_F$



Ta max – $I_{F\,(AV)}$



$r_{th\,(j\text{-}a)} - t$



Surge forward current (non-repetitive)

